US 20240213409A1

(19) **United States**

(12) **Patent Application Publication** (10) **Pub. No.: US 2024/0213409 A1**

ALTAZIN et al. (43) **Pub. Date: Jun. 27, 2024**

(54) **METHOD FOR MANUFACTURING MICRO-LEDS**

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(21) Appl. No.: **18/541,109**

(22) Filed: **Dec. 15, 2023**

(30) **Foreign Application Priority Data**

Dec. 21, 2022 (FR) 22 14156

Publication Classification

(51) **Int. Cl.**

H01L 33/32	(2006.01)
H01L 25/075	(2006.01)
H01L 33/00	(2006.01)
H01L 33/20	(2006.01)
H01L 33/38	(2006.01)
H01L 33/42	(2006.01)

(52) **U.S. Cl.**

CPC ***H01L 33/32*** (2013.01); ***H01L 25/0753*** (2013.01); ***H01L 33/007*** (2013.01); ***H01L 33/20*** (2013.01); ***H01L 33/382*** (2013.01); ***H01L 33/42*** (2013.01); *H01L 2933/0016* (2013.01)

(57) **ABSTRACT**

Method for manufacturing micro-LEDs comprising the following steps:

i) providing a stack comprising at least one strongly n-doped GaN layer (**104**), an n-doped GaN layer (**105**), quantum wells (**106**) and a p-doped GaN layer (**107**),

ii) porosifying the GaN layer (**104**), to obtain a porosified GaN layer (**104'**),

iii) forming mesas in the stack,

iv) covering the porosified GaN layer (**104'**) with a second electrode (**301**) or with an encapsulation layer (**302**), the second electrode (**301**) or the encapsulation layer (**302**) being in direct contact with the porosified GaN layer (**104'**).

step ii) being carried out so that the optical index of the porosified GaN layer (**104'**) does not vary by more than 10% with respect to the optical index of the second electrode (**301**) and/or with respect to the optical index of the encapsulation layer (**302**).